Advanced RF/Baseband Interconnects for Future ULSI Communications

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Abstract

Future inter- and intra-ULSI interconnect systems demand extremely high data rates as well as bi-directional multi-I/O concurrent service, re-configurable computing/processing architecture, and total compatibility with mainstream silicon SOC (system-on-chip) and SIP (system-in-package) technologies. In this paper, we review recent advances in CDMA and FDMA interconnect schemes that promise to meet all of the above system requirements. The physical transmission line is no longer limited to a direct-coupled metal wire. Rather, it can be accomplished via either wired or wireless mediums through capacitor couplers that reduce the baseband noise and DC power consumption. These new advances in interconnect schemes would fundamentally alter the paradigm of ULSI data communications and enable the design of next generation computing/processing systems.

Introduction

The system performance of modern ULSI is being limited by its interconnect bandwidth in both on-chip and chip-to-chip communications [1-3]. The rapid evolution of ULSI has demanded that the interconnect system be fast and at the same time be flexible, reliable and low cost. Ideally, future interconnect systems must encompass the following important features:

- Ultra-high data rates (e.g. >100Gbps/pin or 20Tbps aggregate [2], defined as the total sum of data rate for each pin on a chip or within a system of chips)
- Concurrent multi-I/O's service for simultaneous and bidirectional communications on a shared transmission medium
- Realtime re-configurability in connectivity and bandwidth for optimized channel efficiency and fault-tolerance

Additionally, the fabrication of future interconnect systems must be compatible with the mainstream SOC and SIP technologies for low cost system production.

Traditional inter-chip and intra-chip communications are based solely on TDMA (time division multiple access). In a TDMA-interconnect (*TDMA-I*) system, each I/O pair communicates over a shared transmission medium by transmitting only during its scheduled time slot in which no other I/O pair may transmit. In essence, time is being divided or allocated to each individual I/O pair so that a given transmission medium may be effectively shared. Furthermore, advanced *TDMA-I* (bus and links) in recent years has exploited multi-level signaling and dispersive signal equalization techniques to achieve multi-Gbps throughput [4-6]. Nevertheless, this type of system is limited to fixed and non-reconfigurable architecture that has high data transmission latency and cannot support bidirectional and simultaneous transmission of multiple I/Os on the same physical channel.

Advanced Interconnect Schemes

To overcome the limitations of traditional TDMA-I, a number of new interconnect schemes have been investigated recently to greatly increase the aggregate data rate and concurrency as well as to reduce latency and power consumption [7-13]. These new schemes permit the use of a combination of other multiple access techniques, namely code division multiple access (CDMA) and frequency division multiple access (FDMA). In CDMA interconnect (CDMA-I), each I/O pair is assigned one or more pseudo-noise (PN) codes with near-ideal correlation property so that any other I/O pair assigned with different PN codes will contribute no interference when they are transmitting concurrently onto the same medium. In contrast, FDMA-I allows sharing of a transmission medium by assigning I/O's to different frequency channels. I/O's assigned with different frequency channels may communicate concurrently with virtually no interference, provided that undesired frequency channels for a given I/O are filtered out properly. FDMA-I and CDMA-I may be combined into a multicarrier CDMA-I, whereby concurrent I/O transmissions are accomplished by properly assigning codes and frequencies to each I/O pair.

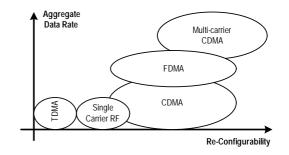


Fig. 1 Comparison of Interconnect Schemes

Figure 1 compares new schemes based on *CDMA-I* and *FDMA-I* against the traditional *TDMA-I* in terms of two critical features for interconnects used in future ULSI systems: namely, aggregate data rate and re-configurability. Interconnect systems based on the *multi-carrier CDMA-I* achieve the highest aggregate data rate and re-configurability. The high aggregate data rate is a result of the increased bandwidth made available through the use of more than one frequency channel. The high re-configurability arises from the increased number of combined code and frequency channels (or N_c and N_f , which denote

respectively the number of code channels and the number of frequency channels) now available to the system to dynamically assign based on the specific operation requirement. Note that both *FDMA-I* and *CDMA-I* have similar degrees of reconfigurability but *FDMA-I* has higher aggregate data rates than *CDMA-I* due to the additional bandwidth made available through multiple frequency channels. In theory, *TDMA-I* has the same degree of re-configurability as either *FDMA-I* or *CDMA-I* in that a *TDMA-I* scheme can re-configure based on rescheduling and reassigning time slots for a given set of I/O's depending on the operation needs. In principle, the number of time slot N_t can be made equal to N_c or N_f . However, even

though an increase in N_t results in proportional reduction in the average data rate per I/O pin, the burst data rate for each I/O pin still remains the same as the aggregate data rate. The high I/O bust data rate makes implementation difficult due to the need for high-order modulation and time-domain equalizers at high operating speed. For *CDMA-I* and *FDMA-I*, on the other

hand, the burst data rate per I/O is inversely proportional to N_c

and N_f , which simplifies the signal processing required for

each I/O. In particular, for *CDMA-I*, Rake receiver architecture may be employed to compensate for time dispersion in the transmission media but it requires much less complexity than a time-domain equalizer [14]. To put this into the perspective of practical implementation, wired *TDMA-I* has limited reconfigurability due to difficulty in increasing N_t without excessive complexity and power dissipation in the transceiver system design.

The re-configurability of wired *TDMA-I* may be improved with the single-carrier RF-interconnect scheme (or *SCRFI*) shown in Fig 1. The *SCRFI* uses only one frequency channel and achieves similar throughput as a wired *TDMA-I* system. However, it is able to achieve higher re-configurability than *TDMA-I*, since the transmission medium is no longer limited to fixed wiring but rather may be wirelessly broadcasted through coupling capacitors to communicate with different receivers. Such a scheme not only simplifies the fabrication process by eliminating the vertical metal studs needed in future 3D IC but also reduces the noise and DC power consumption. Transmission through capacitor-coupling can also be applied to *FDMA-I*, *CDMA-I*, and *Multi-Carrier CDMA-I* (or *MCCDMA-I*) as well.

Conclusion

In this paper, we will review recent progress in each of the new interconnect schemes described in Fig. 1 and discuss their applications in future ULSI interconnect implementations and architecture designs of next generation computer/processor systems. We will first describe a wired *CDMA-I* that achieves channel re-configurability while providing simultaneous multi-I/O's services. We will then discuss the wired *FDMA-I* that is able to achieve multi-band (or multi-mode) channel communications. Subsequently, *SC-RFI* specifically designed for 3D IC will be presented. Finally, wireless inter-chip communication based on *MCCDMA-I* will be discussed along with other system applications such as CDMA dynamic random access memory (*CDMA-DRAM*) and re-configurable interconnect for next generation systems (*RINGS*).

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Advanced RF/Baseband Interconnects for Inter- and Intra-ULSI Communications

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Future Interconnect System Requirements

- Ultra-high data rates (>100Gbps/pin or 20Tbps aggregate, defined as total sum of data rate for each pin or within a system of chips) and low latency
- Concurrent multi-I/O's service for simultaneous/bidirectional communications on a shared transmission medium
- Realtime reconfigurability in connectivity and bandwidth for optimized channel efficiency and faulttolerance

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 Compatible with mainstream SOC and SIP technologies for low cost system insertion

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Advanced Interconnect Schemes

- CDMA-I
 - Code divided channels (N_c) based on direct sequence spread spectrum (DSSS)
 - Flexible in reconfiguration by software code assignment
- FDMA-I
 - Frequency divided channels (N_f)
 - Data rate for individual channel proportional to its bandwidth allocation
- Combined FDMA/CDMA-I (Multi-Carrier CDMA-I)
 - FDMA/CDMA combined multiple access
 Reduced burst rate per channel leads to low transceiver complexity and low
 power consumption
 - Synchronous access can be realized by using orthogonal codes to eliminate the cross channel interference

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Issues of Traditional TDMA Interconnect (*TDMA-I*)

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Outline

Future Interconnect System Requirements

□ Issues of Traditional TDMA-Interconnect

New Interconnects System Applications

Advanced Interconnects

- CDMA-Interconnect - FDMA-Interconnect

- FDMA/CDMA-Interconnect

Comparison of Interconnects

Summary

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- Space/Time multiplexing only, does not offer concurrent and bi-directional communications for distributed multi-I/Os
- High I/O burst data rate (equals aggregate data rate) demands high-order modulation and time-domain equalization
- Limited reconfigurability because rescheduling or reassigning N_t (number of time slots) inevitably increases the complexity and power consumption of transceiver system
- · Difficult to re-allocate bandwidth to each I/O pair in realtime
- · Switched by hardware, cannot take full advantage of packet switching
- · Poor security, source-destination pairs physically identifiable on wafer
- Large number of I/Os, inefficient use of wafer real estate due to bonding, soldering and packaging constraints

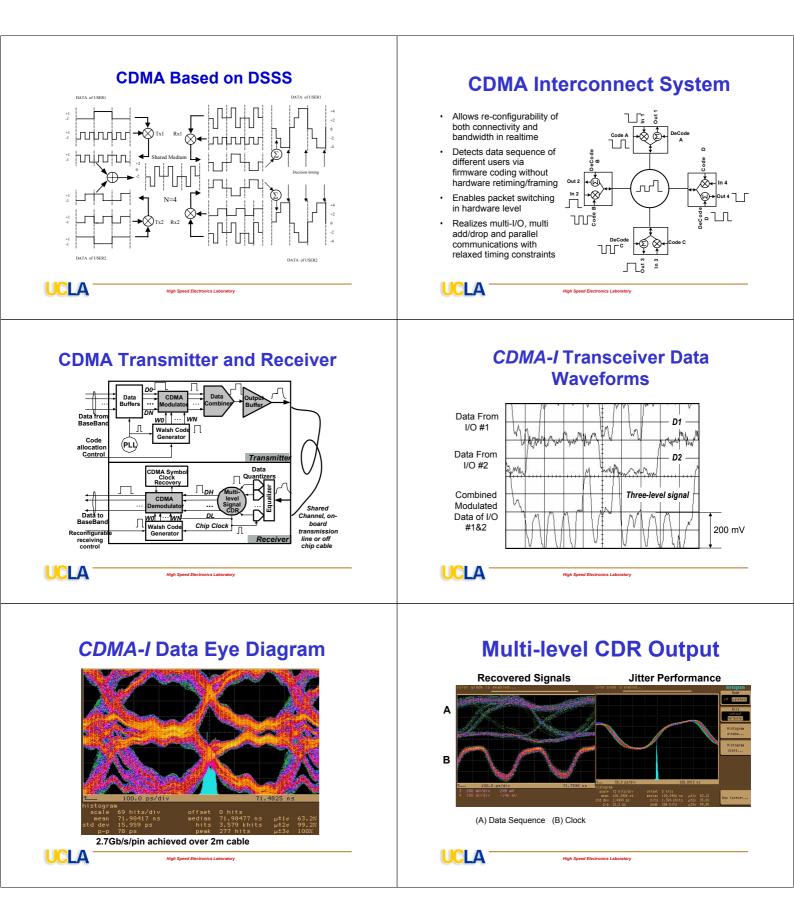
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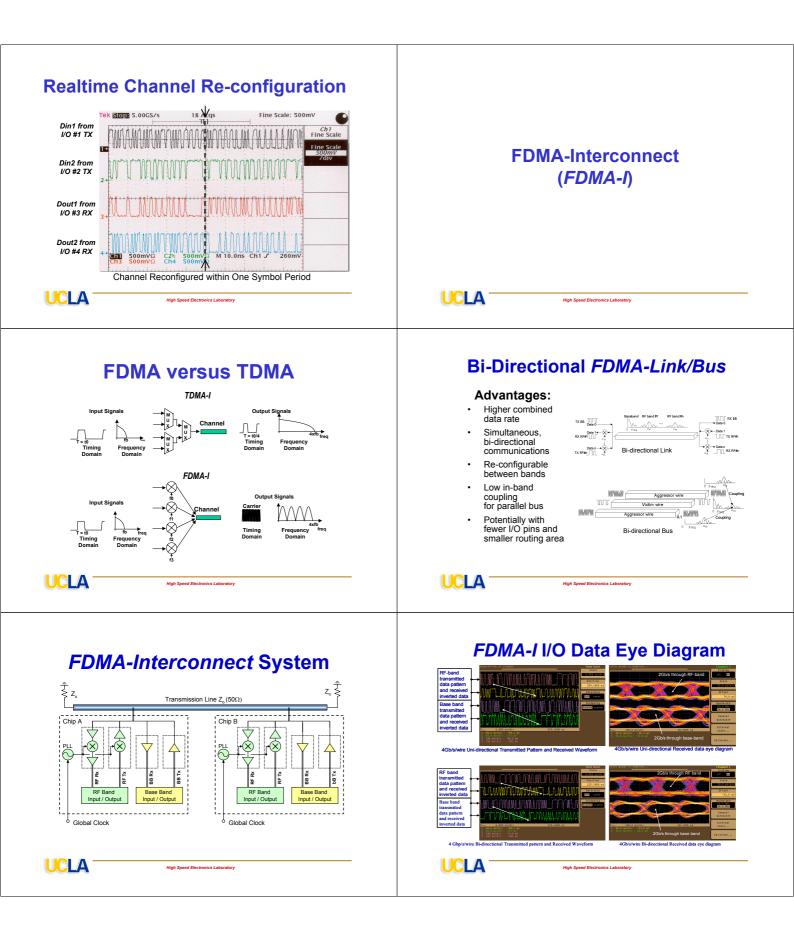
- · Inadequate line shielding, vulnerable to noise and interference
- · Low dynamic testability for "known-good-die"

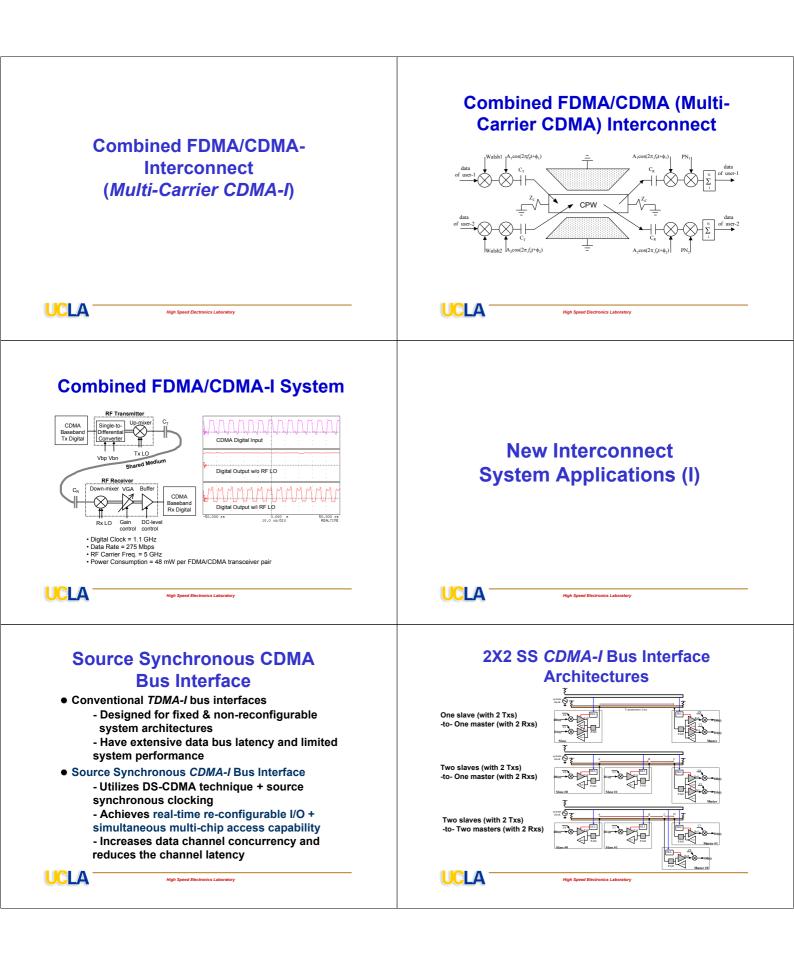
CDMA-Interconnect (CDMA-I)

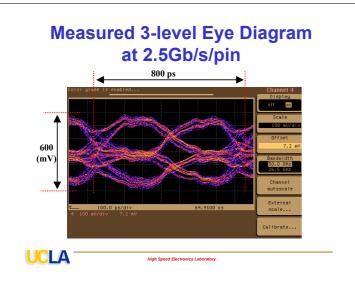
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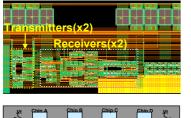








SS CDMA-I Bus Transceiver and Test module



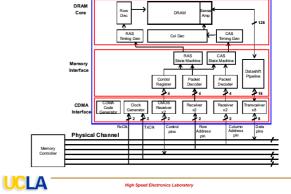
50 ohm Terminated Transmission line

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□ The new chip is being fabricated in SAMSUNG 0.10-um **DRAM Process** and packaged in a WBGA

Test PCB module with four (2X2) chips T onition pins





Comparison of DRAM Bus Interface Standard

	# of Parallel high-speed Data Channels	# of Parallel High-speed Address Channels	# of Parallel High-speed Clock Channels	Total # of High- speed Data & Add. Channels	Min. # of Shielding Channels for Data & Add.	Data Rate (Mbps)	Total Data Bandwidth
SDRAM (PC-133)	<u>64</u>	12	1	<u>76</u>	-	133	<u>1.1 Gbyte/s</u>
Rambus DRAM	<u>16</u>	8	2 (differential)	24	24	400 * 2	<u>1.6 Gbyte/s</u>
DDR(SSTL-2)	<u>64</u>	12	8 (data strobe)	<u>76</u>	-	133 * 2	2.1 Gbyte/s
CDMA DRAM	4	2	2 (differential)	<u>6</u>	<u>6</u>	800 * 4	<u>1.6 Gbyte/s</u>

RDRAM uses 2 differential (CTM/CTMB.CFM/CFMB) clock lines for source synchronous clocking DDR uses 8 data strobe (DQS) lines for source synchronous clocking CDMA DRAM can use 2 differential clock or CDR for source synchronous clocking Both SDRAM and DDR DRAM has some additional command lines which are not listed above

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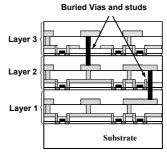
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New Interconnect System Applications (II)

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Vertical Interconnect in 3D Integration

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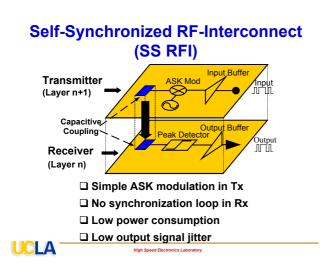
Courtesy: Prof. Jason Woo, UCLA

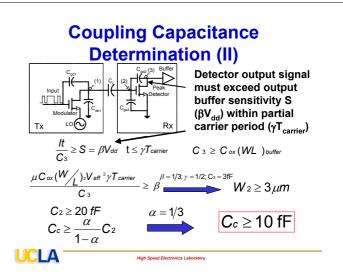
Issues:

Traditional 3D integration requires complex etching/alignment /metallization for vias and studs

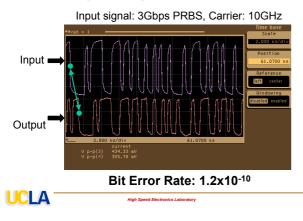
Solution:

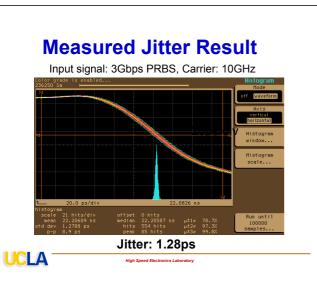
Use capacitor-coupled **RF-Interconnect to avoid** complex processing



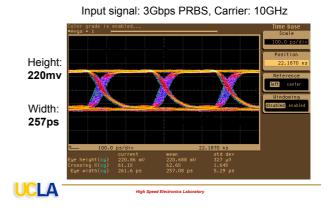


Output/Input Waveforms





Output Signal Eye Diagram

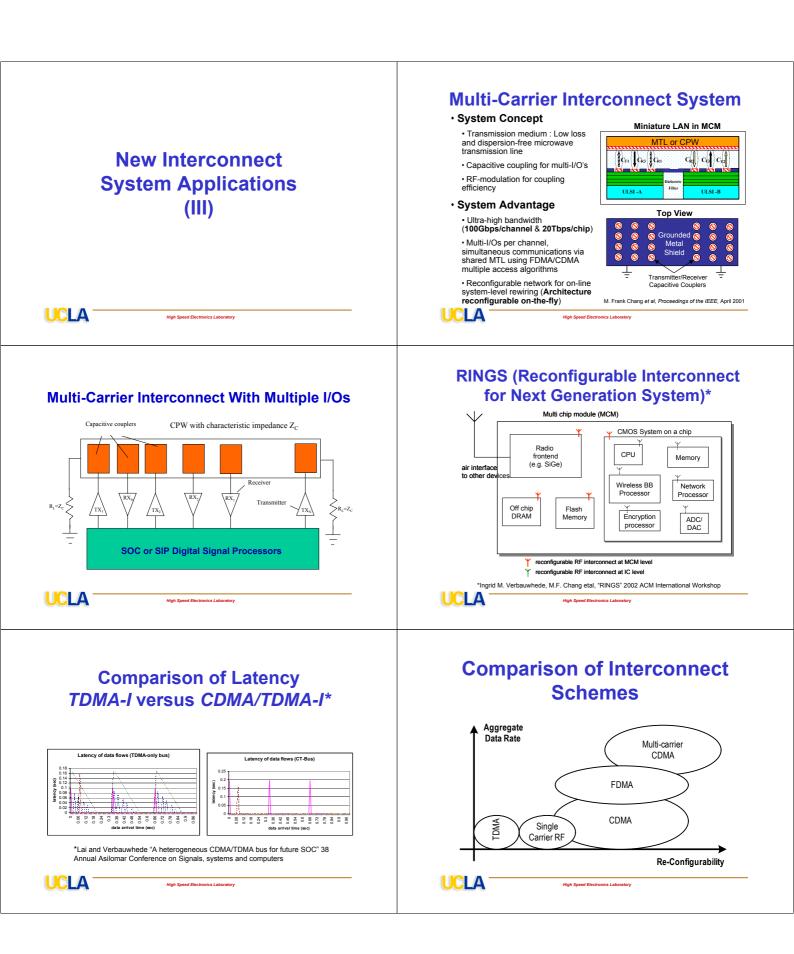


SS RFI Performance

PRBS Input Signal	3Gbps		
Carrier	10GHz		
Jitter	1.28ps rms		
BER	1.2x10 ⁻¹⁰		
Coupling Capacitance	60fF		
Active Chip Area	0.02mm ²		
Power Consumption	4mW from 1.8V supply		

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Summary

- Traditional *TDMA-I* does not meet future SOC/SIP interconnect needs in dynamic channel/bandwidth re-allocation, concurrent simultaneous multi-I/O service and bi-directional communications on shared transmission medium
- New Interconnects based on additional CDMA and FDMA algorithms (*CDMA-I, FDMA-I and Multi-Carrier CDMA-I*) can satisfy the above needs and would alter the paradigm of ULSI data communications and enable reconfigurable architecture designs for future computing/processing systems



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